# Phototransistor, side view type RPM-25PT

The RPM-25PT is a silicon planar phototransistor in a side-facing package with two-phase output. This device is particularly suited for use with a ROHM SIM-22ST infrared light emitting diode.

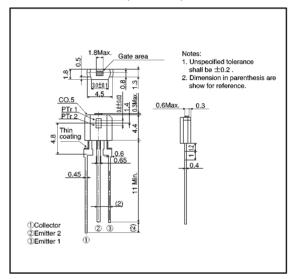
#### Applications

Optical control equipment

#### Features

- 1) High sensitivity.
- 2) Two-phase output.
- 3) Side-facing detector.

#### External dimensions (Units: mm)



### ● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector-emitter voltage	VCEO	30	V
Emitter-collector voltage	VECO	4.5	٧
Collector current	lc	30	mA
Collector power dissipation	Pc	100	mW
Operating temperature	Topr	-25~ <del>+</del> 85	°C
Storage temperature	Tstg	-30~+100	°C

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# ●Electrical and optical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Light current	lc1,lc2	25	_	100	μΑ	VcE=5V, E=500Lx
Dark current	ICEO	_	_	0.5	μΑ	VcE=10V(Black box)
Peak sensitivity wavelength	λp	_	800	_	nm	_
Collector-emitter saturation voltage	VCE(sat)	_	_	0.4	٧	Ic=25 μA, E=500Lx
Dispersion for sensitivity	Ic1 / Ic2	8.0	1.0	1.2	_	_
Response time	tr • tf	_	10	_	μS	VcE=5V, Ic=1mA, RL=100 Ω

# Electrical and optical characteristic curves

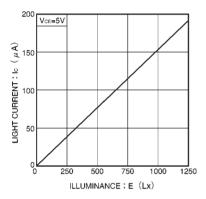


Fig.1 Collector current vs. emitting strength

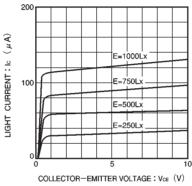


Fig.2 Output characteristics

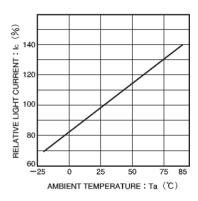


Fig.3 Relative output vs. ambient temperature

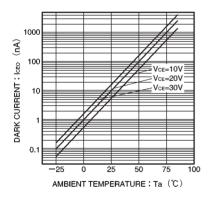


Fig.4 Dark current vs. ambient temperature

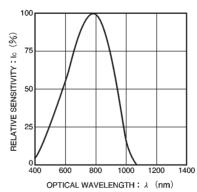


Fig.5 Spectral sensitivity

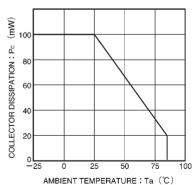


Fig.6 Collector dissipation vs. ambient temperature

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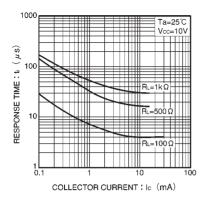


Fig.7 Response time vs. collector current

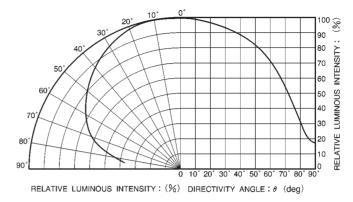


Fig.8 Directional pattern